N-Channel Enhancement Mode Field Effect Transistor

Product Summary

● V_{DS}	60V
● I_D	3A

● D/F2 1/F2 1Tm0 gTmr9((nn)4ON)000008882 0 596.04 842.04 reW* n

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■ Electrical Characteristics (T_J=25 unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}= 0V, I_D=250μA	60	-	-	

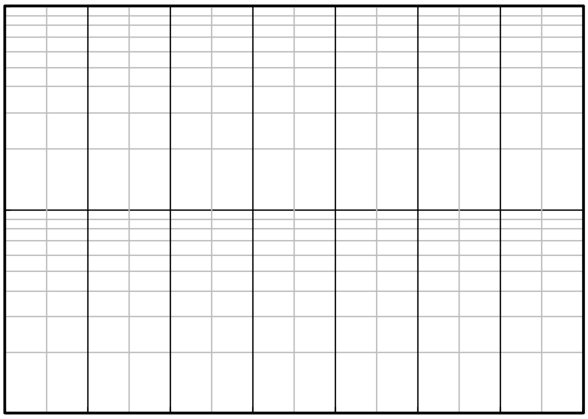
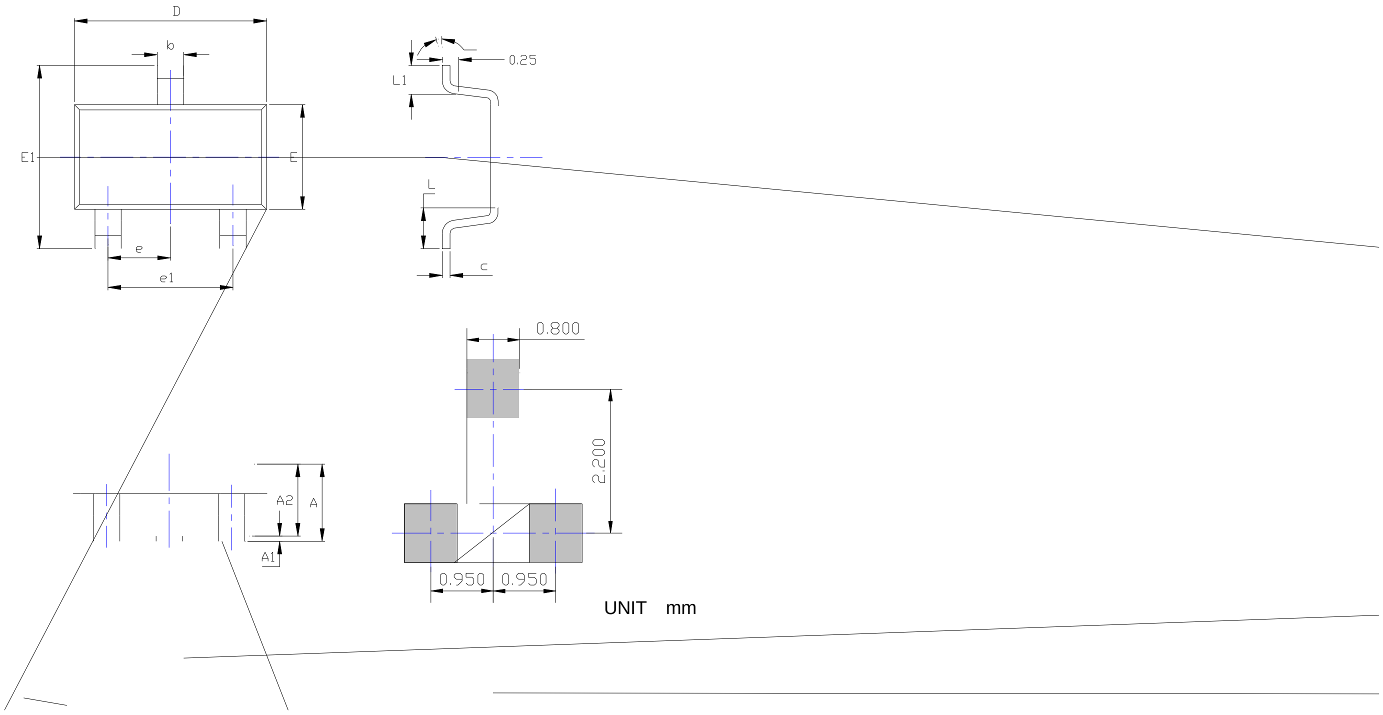


Figure 7. $R_{DS(on)}$

■ SOT-23-3L Package information



UNIT mm

Disclaimer

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The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of with would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Yangj oce94 Tm0 g0 G9t4ere nuclear